

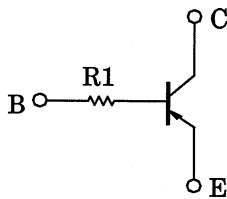
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2010,RN2011

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1010, RN1011

Equivalent Circuit



Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C *	400	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55~150	°C

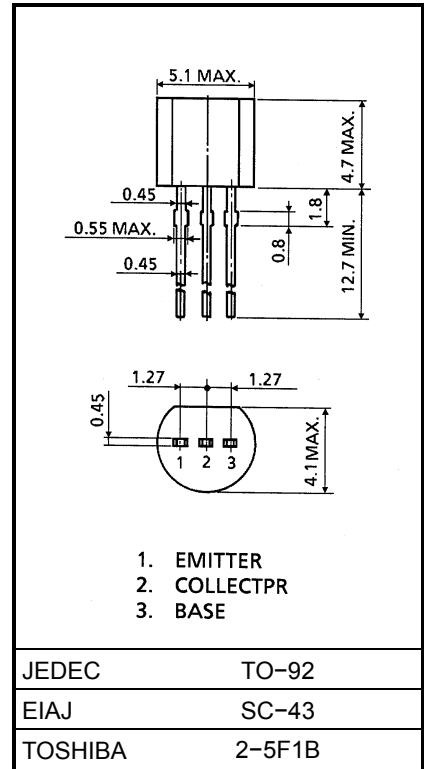
Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I _{CBO}	—	V _{CB} = -50V, I _E = 0	—	—	-100	nA
Emitter cut-off current	I _{EBO}	—	V _{EB} = -5V, I _C = 0	—	—	-100	nA
DC current gain	h _{FE}	—	V _{CE} = -5V, I _C = -1mA	120	—	400	
Collector-emitter saturation voltage	V _{CE (sat)}	—	I _C = -5mA, I _B = -0.25mA	—	-0.1	-0.3	V
Transition frequency	f _T	—	V _{CE} = -10V, I _C = -5mA	—	200	—	MHz
Collector output capacitance	C _{ob}	—	V _{CB} = -10V, I _E = 0, f = 1MHz	—	3	6	pF
Input resistor	RN2010	R1	—	3.29	4.7	6.11	kΩ
	RN2011			7	10	13	

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Unit: mm



Weight: 0.21g

